



THE DATASHEET OF BZV55C33



- ZENER DIODES
- LEADLESS PACKAGE FOR SURFACE MOUNT
- DOUBLE PLUG CONSTRUCTION
- METALLURGICALLY BONDED

**BZV55 C2V4
thru
BZV55 C75**

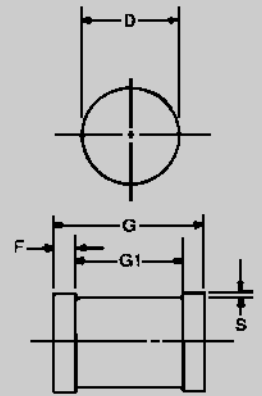
MAXIMUM RATINGS

Operating Temperature: -65°C to +175°C
 Storage Temperature: -65°C to +175°C
 Power Derating: 3.33 mW / °C above +50°C
 Forward Voltage: @ 200mA: 1.1 Volts maximum

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified.

TYPE	ZENER VOLTAGE (NOTE 1) V _Z @ I _{ZT}			MAXIMUM DIFFERENTIAL RESISTANCE r _{diff} @ I _Z		MAXIMUM REVERSE CURRENT I _R @ V _R	
	VOLTS MIN	VOLTS MAX	mA	OHMS	mA	μA	VOLTS
BZV55 C2V4	2.2	2.6	5	100	5	50	1
BZV55 C2V7	2.5	2.9	5	100	5	20	1
BZV55 C3V0	2.8	3.2	5	95	5	10	1
BZV55 C3V3	3.1	3.5	5	95	5	5	1
BZV55 C3V6	3.4	3.8	5	90	5	5	1
BZV55 C3V9	3.7	4.1	5	90	5	3	1
BZV55 C4V3	4.0	4.6	5	90	5	3	1
BZV55 C4V7	4.4	5.0	5	80	5	3	2
BZV55 C5V1	4.8	5.4	5	60	5	2	2
BZV55 C5V6	5.2	6.0	5	40	5	1	2
BZV55 C6V2	5.8	6.6	5	10	5	3	4
BZV55 C6V8	6.4	7.2	5	15	5	2	4
BZV55 C7V5	7.0	7.9	5	15	5	1	5
BZV55 C8V2	7.7	8.7	5	15	5	.700	5
BZV55 C9V1	8.5	9.6	5	15	5	.500	6
BZV55 C10	9.4	10.6	5	20	5	.200	7
BZV55 C11	10.4	11.6	5	20	5	.100	8
BZV55 C12	11.4	12.7	5	25	5	.100	8
BZV55 C13	12.4	14.1	5	30	5	.100	8
BZV55 C15	13.8	15.6	5	30	5	.050	10.5
BZV55 C16	15.3	17.1	5	40	5	.050	11.2
BZV55 C18	16.8	19.1	5	45	5	.050	12.6
BZV55 C20	18.8	21.2	5	55	5	.050	14.0
BZV55 C22	20.8	23.3	5	55	5	.050	15.4
BZV55 C24	22.8	25.6	5	70	5	.050	16.8
BZV55 C27	25.1	28.9	2	80	2	.050	18.9
BZV55 C30	28.0	32.0	2	80	2	.050	21.0
BZV55 C33	31.0	35.0	2	80	2	.050	23.1
BZV55 C36	34.0	38.0	2	90	2	.050	25.2
BZV55 C39	37.0	41.0	2	130	2	.050	27.3
BZV55 C43	40.0	46.0	2	150	2	.050	30.1
BZV55 C47	44.0	50.0	2	170	2	.050	32.9
BZV55 C51	48.0	54.0	2	180	2	.050	35.7
BZV55 C56	52.0	60.0	2	200	2	.050	39.2
BZV55 C62	58.0	66.0	2	215	2	.050	43.4
BZV55 C68	64.0	72.0	2	240	2	.050	47.6
BZV55 C75	70.0	79.0	2	255	2	.050	52.2

NOTE 1 Nominal Zener voltage is measured with the device junction in thermal equilibrium at an ambient temperature of 25°C ± 3°C.



	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
D	1.60	1.70	0.063	0.067
F	0.41	0.55	0.016	0.022
G	3.30	3.70	.130	.146
G1	2.54 REF.		.100 REF.	
S	0.03 MIN.		.001 MIN.	

DESIGN DATA

CASE: DO-213AA, Hermetically sealed glass case. (MELF, SOD-80, LL34)

LEAD FINISH: Tin / Lead

THERMAL RESISTANCE: (R_{QJEC}): 100 °C/W maximum at L = 0 inch

THERMAL IMPEDANCE: (Z_{QJX}): 35 °C/W maximum

POLARITY: Diode to be operated with the banded (cathode) end positive.

MOUNTING SURFACE SELECTION: The Axial Coefficient of Expansion (COE) Of this Device is Approximately +6PPM/°C. The COE of the Mounting Surface System Should Be Selected To Provide A Suitable Match With This Device.



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